74HC157-Q100; 74HCT157-Q100

Quad 2-input multiplexer

Rev. 1 — 2 August 2012 Product data sheet

1. General description

The 74HC157-Q100; 74HCT157-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL. It is specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT157-Q100 are quad 2-input multiplexers which select 4 bits of data from two sources under the control of a common data select input (S). The enable input ($\overline{E}$) is active LOW. When $\overline{E}$ is HIGH, all of the outputs (1Y to 4Y) are forced LOW regardless of all other input conditions.

Moving the data from two groups of registers to four common output buses is a common use of the 74HC/HCT157-Q100. The state of the common data select input (S) determines the particular register from which the data comes. It can also be used as function generator. The device is useful for implementing highly irregular logic by generating any four of the 16 different functions of two variables with one variable common. The 74HC/HCT157-Q100 is logic implementation of a 4-pole, 2-position switch, where the position of the switch is determined by the logic levels applied to S.

The logic equations are:

$$1Y = \overline{E} \times (1I1 \times S + 1I0 \times \overline{S})$$
$$2Y = \overline{E} \times (2I1 \times S + 2I0 \times \overline{S})$$
$$3Y = \overline{E} \times (3I1 \times S + 3I0 \times \overline{S})$$
$$4Y = \overline{E} \times (4I1 \times S + 4I0 \times \overline{S})$$

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Low-power dissipation
- Non-inverting data path
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC157D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT157D-Q100				
74HC157PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT157PW-Q100				
74HC157BQ-Q100	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74HCT157BQ-Q100				

4. Functional diagram

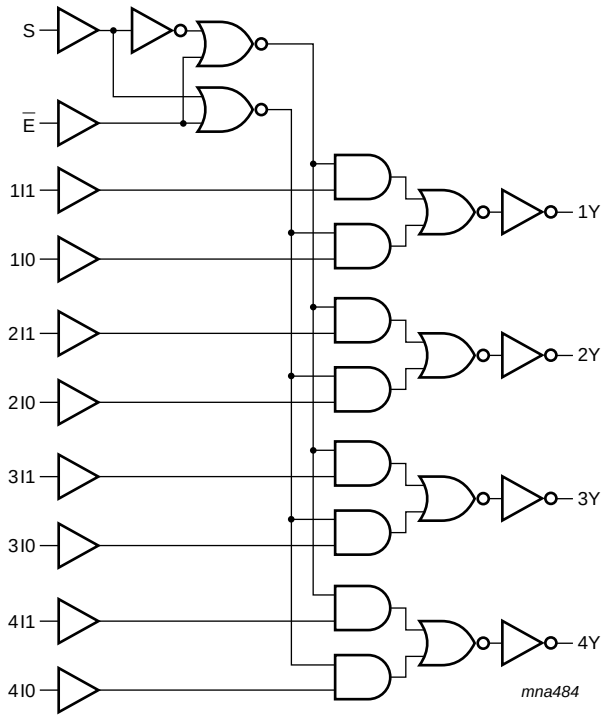


Fig 1. Logic diagram

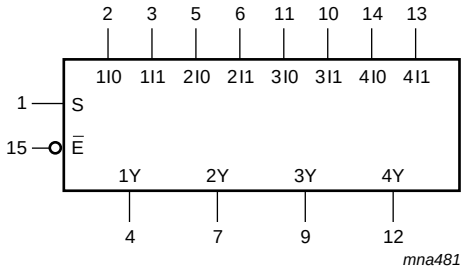


Fig 2. logic symbol

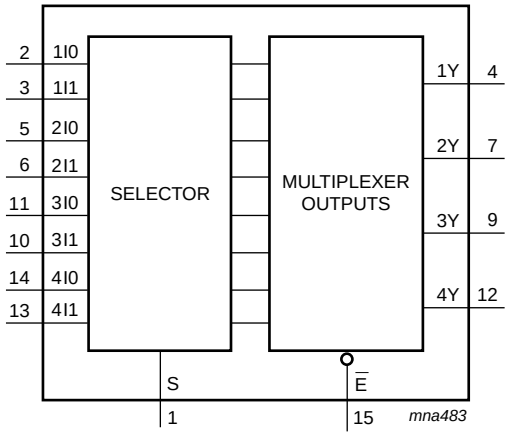


Fig 3. Logic symbol

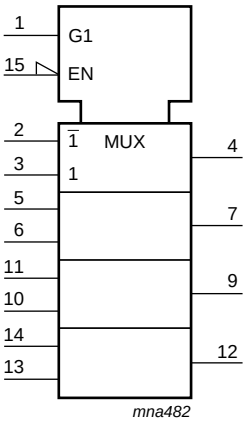


Fig 4. IEC logic symbol

5. Pinning information

5.1 Pinning

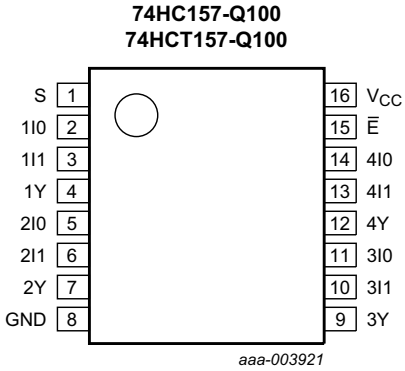
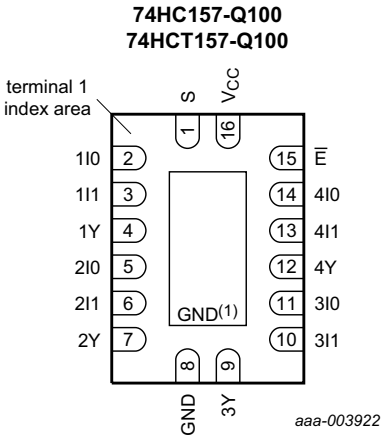


Fig 5. Pin configuration SO16, TSSOP16



Transparent top view

(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 6. Pin configuration DHVQFN16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
S	1	common data select input
1I0 to 4I0	2, 5, 11, 14	data inputs from source 0
1I1 to 4I1	3, 6, 10, 13	data inputs from source 1
1Y to 4Y	4, 7, 9, 12	multiplexer outputs
GND	8	ground (0 V)
$\overline{E}$	15	enable input (active LOW)
V_{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Input				Output
$\overline{E}$	S	nI0	nI1	nY
H	X	X	X	L
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

[1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)		-	±25	mA
I_{CC}	supply current			-	+50	mA
I_{GND}	ground current			-	–50	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C				
	SO16 package		[1]	-	500	mW
	TSSOP16 package		[2]	-	500	mW
	DHVQFN16 package		[3]	-	500	mW

[1] P_{tot} derates linearly with 8 mW/K above 70 °C.

[2] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[3] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC157-Q100			74HCT157-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +85 °C		T_{amb} = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC157-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = –4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = –5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +85 °C		T_{amb} = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	µA
C_I	input capacitance		-	3.5	-					pF
74HCT157-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = –20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 µA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	8.0	-	80	-	160	µA
ΔI_{CC}	additional supply current	$V_I = V_{CC}$ – 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; I_O = 0 A								
		per input pin; nIn inputs	-	100	360	-	450	-	490	µA
		per input pin; $\overline{E}$ input	-	60	216	-	270	-	294	µA
		per input pin; S input	-	100	360	-	450	-	490	µA
C_I	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 9.

Symbol	Parameter	Conditions		T_{amb} = 25 °C			T_{amb} = –40 °C to +85 °C		T_{amb} = –40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
For type 74HC157-Q100											
t_{pd}	propagation delay	nI0, nI1 to nY; see Figure 7	[1]								
		V_{CC} = 2.0 V		-	36	125	-	155	-	190	ns
		V_{CC} = 4.5 V		-	13	25	-	31	-	38	ns
		V_{CC} = 5 V; C_L = 15 pF		-	11	-	-	-	-	-	ns
		V_{CC} = 6.0 V		-	10	21	-	26	-	32	ns
		S to nY; see Figure 7	[1]								
		V_{CC} = 2.0 V		-	41	125	-	155	-	190	ns
		V_{CC} = 4.5 V		-	15	25	-	31	-	38	ns
		V_{CC} = 5 V; C_L = 15 pF		-	12	-	-	-	-	-	ns
		V_{CC} = 6.0 V		-	12	21	-	26	-	32	ns
		$\overline{E}$ to nY; see Figure 8	[1]								
		V_{CC} = 2.0 V		-	39	115	-	145	-	175	ns
		V_{CC} = 4.5 V		-	14	23	-	29	-	35	ns
		V_{CC} = 5 V; C_L = 15 pF		-	11	-	-	-	-	-	ns
		V_{CC} = 6.0 V		-	11	20	-	25	-	30	ns
t_t	transition time	nY; see Figure 7	[2]								
		V_{CC} = 2.0 V		-	19	75	-	95	-	110	ns
		V_{CC} = 4.5 V		-	7	15	-	19	-	22	ns
		V_{CC} = 6.0 V		-	6	13	-	16	-	19	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V_I = GND to V_{CC}	[3]	-	70	-	-	-	-	-	pF
For type 74HCT157-Q100											
t_{pd}	propagation delay	nI0, nI1 to nY; see Figure 7	[1]								
		V_{CC} = 4.5 V		-	16	27	-	34	-	41	ns
		V_{CC} = 5 V; C_L = 15 pF		-	13	-	-	-	-	-	ns
		S to nY; see Figure 7	[1]								
		V_{CC} = 4.5 V		-	22	37	-	46	-	56	ns
		V_{CC} = 5 V; C_L = 15 pF		-	19	-	-	-	-	-	ns
		$\overline{E}$ to nY; see Figure 8	[1]								
		V_{CC} = 4.5 V		-	15	26	-	33	-	39	ns
		V_{CC} = 5 V; C_L = 15 pF		-	12	-	-	-	-	-	ns

Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 9.

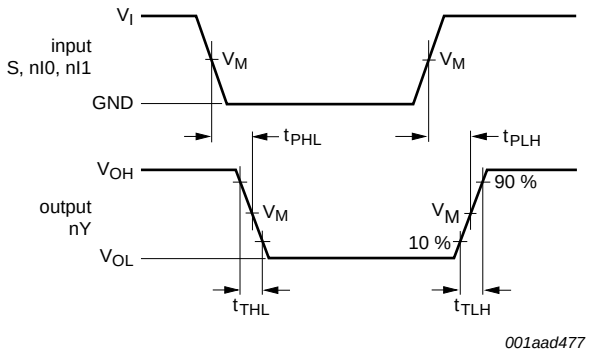
Symbol	Parameter	Conditions		T_{amb} = 25 °C			T_{amb} = –40 °C to +85 °C		T_{amb} = –40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_t	transition time	nY; see Figure 7	[2]								
		V_{CC} = 4.5 V		-	7	15	-	19	-	22	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V_I = GND to V_{CC}	[3]	-	70	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

[2] t_t is the same as t_{THL} and t_{TLH}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

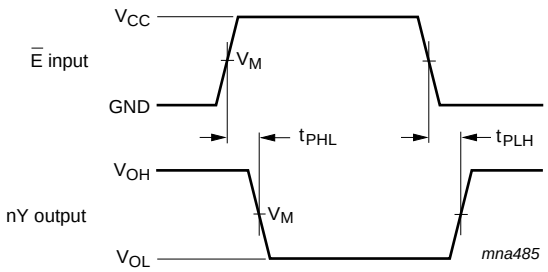
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Propagation delay input (nI0, nI1, S) to output (nYn)



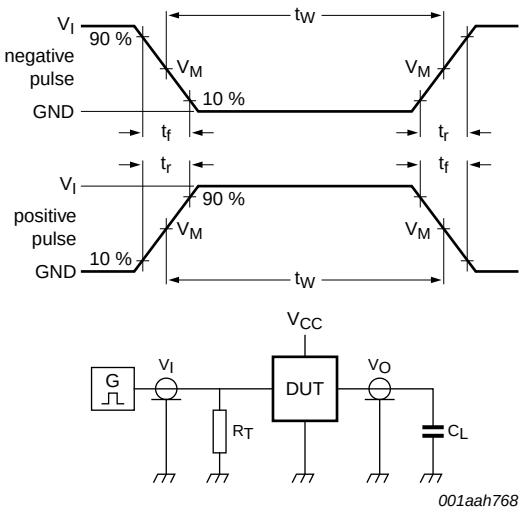
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 8. Propagation delay input ($\overline{E}$) to output (nY)

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC157-Q100	$0.5V_{CC}$	$0.5V_{CC}$
74HCT157-Q100	1.3 V	1.3 V



Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

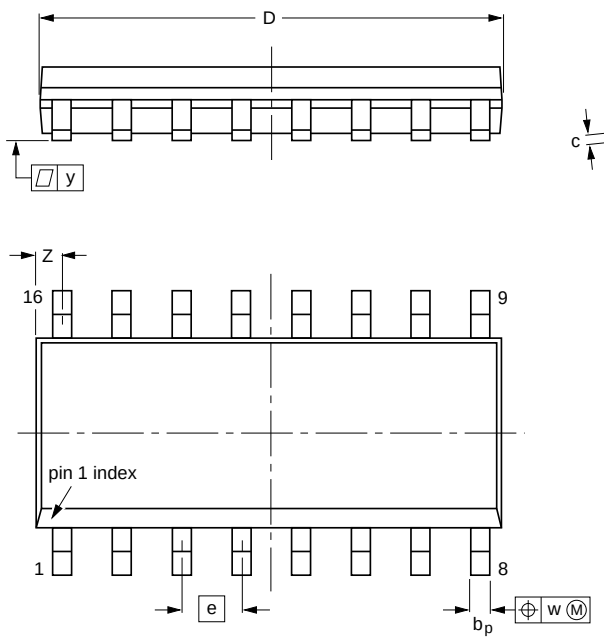
Fig 9. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74HC157-Q100	V_{CC}	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74HCT157-Q100	3.0 V	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

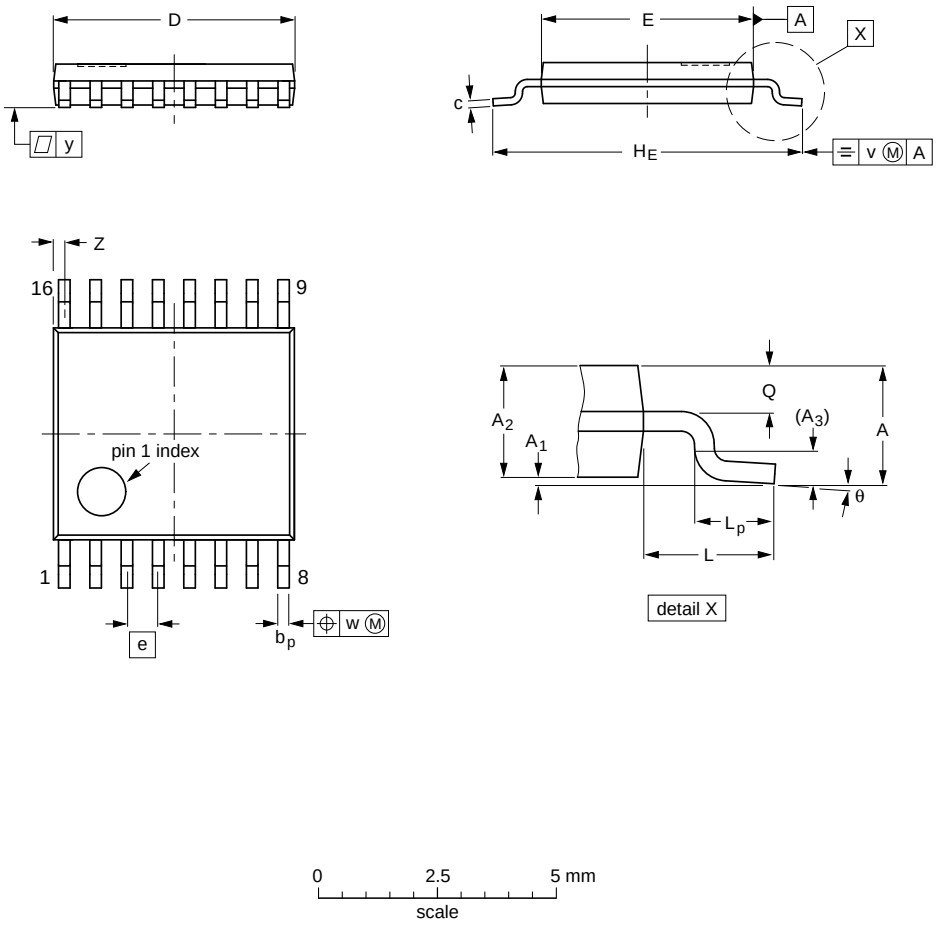
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

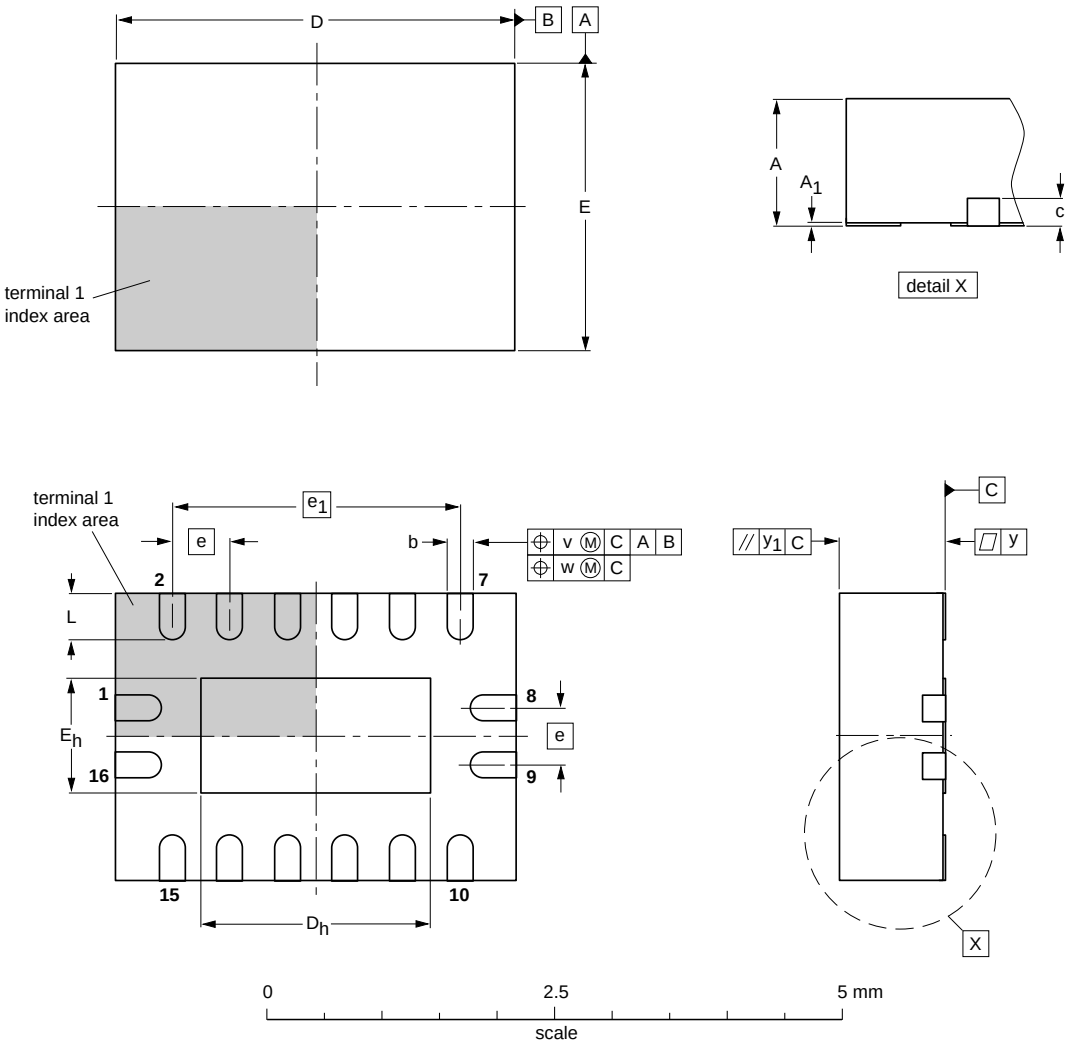
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 11. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm **SOT763-1**



DIMENSIONS (mm are the original dimensions)

UNIT	$A^{(1)}$ max.	A_1	b	c	$D^{(1)}$	D_h	$E^{(1)}$	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 12. Package outline SOT763-1 (DHVQFN16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT157_Q100 v.1	20120802	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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Date of release: 2 August 2012
Document identifier: 74HC_HCT157_Q100